High Voltage, High Current Darlington Transistor Arrays

The seven NPN Darlington connected transistors in these arrays are well suited for driving lamps, relays, or printer hammers in a variety of industrial and consumer applications. Their high breakdown voltage and internal suppression diodes insure freedom from problems associated with inductive loads. Peak inrush currents to 500 mA permit them to drive incandescent lamps.

The MC1413, B with a 2.7 k Ω series input resistor is well suited for systems utilizing a 5.0 V TTL or CMOS Logic. The MC1416, B uses a series 10.5 k Ω resistor and is useful in 8.0 to 18 V MOS systems.



PERIPHERAL DRIVER ARRAYS

SEMICONDUCTOR TECHNICAL DATA

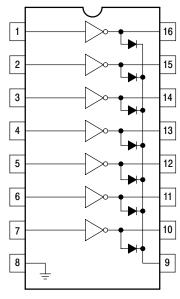


P SUFFIX PLASTIC PACKAGE CASE 648



D SUFFIX PLASTIC PACKAGE CASE 751B (SO–16)

PIN CONNECTIONS

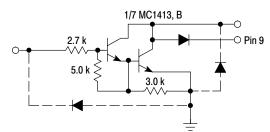


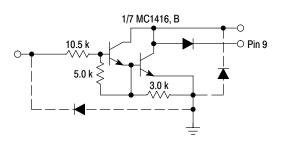
(Top View)

ORDERING INFORMATION

Plastic DIP	SOIC	Operating Temperature Range
MC1413P (ULN2003A) MC1416P (ULN2004A)	MC1413D MC1416D	$T_A = -20^\circ$ to +85°C
MC1413BP MC1416BP	MC1413BD MC1416BD	$T_A = -40^\circ$ to +85°C

Representative Schematic Diagrams





MC1413, B MC1416, B

Rating	Symbol	Value	Unit
Output Voltage	Vo	50	V
Input Voltage	VI	30	V
Collector Current – Continuous	Ι _C	500	mA
Base Current – Continuous	Ι _Β	25	mA
Operating Ambient Temperature Range MC1413–16 MC1413B–16B	T _A	-20 to +85 -40 to +85	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature	TJ	150	°C
Thermal Resistance, Junction–to–Ambient Case 648, P Suffix Case 751B, D Suffix	θ_{JA}	67 100	°C/W

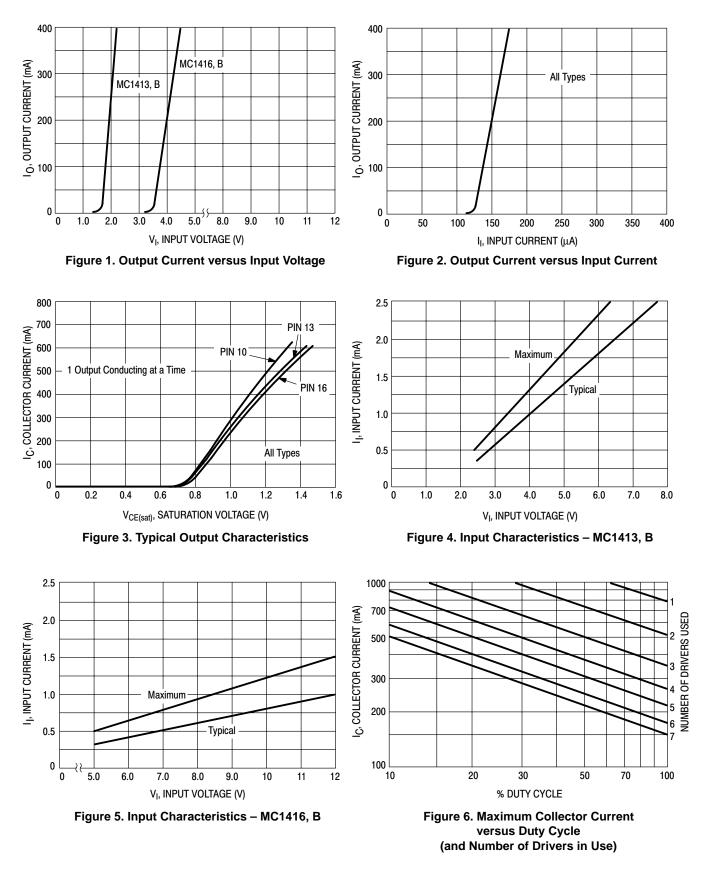
NOTE: ESD data available upon request.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Output Leakage Current $(V_O = 50 \text{ V}, T_A = +85^{\circ}\text{C})$ $(V_O = 50 \text{ V}, T_A = +25^{\circ}\text{C})$ $(V_O = 50 \text{ V}, T_A = +85^{\circ}\text{C}, V_I = 1.0 \text{ V})$	All Types All Types MC1416, B	I _{CEX}	_ _ _	_ _ _	100 50 500	μΑ
Collector–Emitter Saturation Voltage ($I_C = 350 \text{ mA}, I_B = 500 \mu\text{A}$) ($I_C = 200 \text{ mA}, I_B = 350 \mu\text{A}$) ($I_C = 100 \text{ mA}, I_B = 250 \mu\text{A}$)	All Types All Types All Types All Types	V _{CE(sat)}	_ _ _	1.1 0.95 0.85	1.6 1.3 1.1	V
Input Current – On Condition $(V_1 = 3.85 V)$ $(V_1 = 5.0 V)$ $(V_1 = 12 V)$	MC1413, B MC1416, B MC1416, B	I _{I(on)}		0.93 0.35 1.0	1.35 0.5 1.45	mA
Input Voltage – On Condition $(V_{CE} = 2.0 V, I_C = 200 mA)$ $(V_{CE} = 2.0 V, I_C = 250 mA)$ $(V_{CE} = 2.0 V, I_C = 300 mA)$ $(V_{CE} = 2.0 V, I_C = 125 mA)$ $(V_{CE} = 2.0 V, I_C = 200 mA)$ $(V_{CE} = 2.0 V, I_C = 275 mA)$ $(V_{CE} = 2.0 V, I_C = 350 mA)$	MC1413, B MC1413, B MC1413, B MC1416, B MC1416, B MC1416, B MC1416, B	V _{I(on)}		- - - - - -	2.4 2.7 3.0 5.0 6.0 7.0 8.0	V
Input Current – Off Condition ($I_C = 500 \ \mu A, T_A = 85^{\circ}C$)	All Types	I _{I(off)}	50	100	-	μA
DC Current Gain $(V_{CE} = 2.0 \text{ V}, I_C = 350 \text{ mA})$		h _{FE}	1000	-	-	-
Input Capacitance		Cl	-	15	30	pF
Turn–On Delay Time (50% E _I to 50% E _O)		t _{on}	-	0.25	1.0	μs
Turn–Off Delay Time (50% E _I to 50% E _O)		t _{off}	-	0.25	1.0	μs
Clamp Diode Leakage Current (V _R = 50 V)	T _A = +25°C T _A = +85°C	I _R			50 100	μA
Clamp Diode Forward Voltage (I _F = 350 mA)		V _F	-	1.5	2.0	V

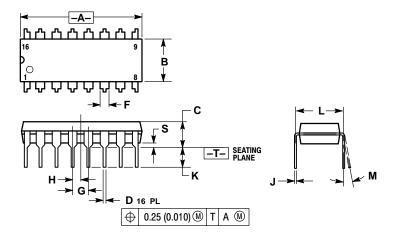
MC1413, B MC1416, B

TYPICAL PERFORMANCE CURVES - T_A = 25°C



OUTLINE DIMENSIONS

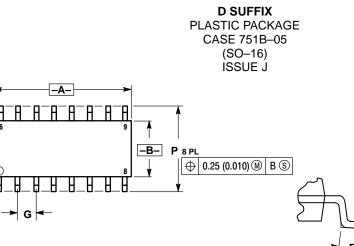
P SUFFIX PLASTIC PACKAGE CASE 648-08 **ISSUE R**



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL. 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH. 5. ROUNDED CORNERS OPTIONAL

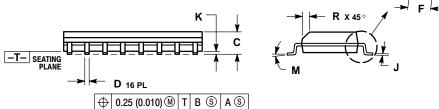
	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
C	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100 BSC 2.54 BSC			BSC	
н	0.050 BSC		1.27 BSC		
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
М	0°	10 °	0 °	10 °	
S	0.020	0.040	0.51	1.01	

OUTLINE DIMENSIONS



A

Н



- NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
Μ	0 °	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

<u>Notes</u>

<u>Notes</u>

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